
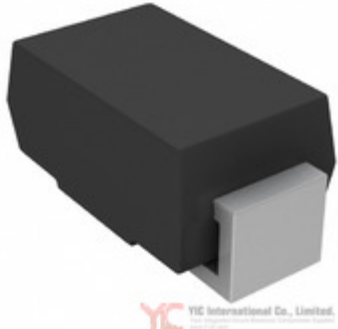




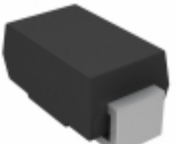
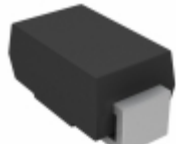

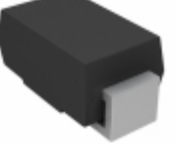

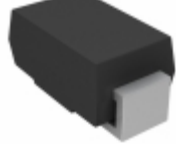
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|---|---|
|  | <p>US1B-E3/5AT</p> |
| | <p>Hersteller-Teilenummer: US1B-E3/5AT</p> <p>Hersteller / Marke: Vishay / Semiconductor - Diodes Division</p> <p>Teil der Beschreibung: DIODE GEN PURP 100V 1A DO214AC</p> <p>Datenblätter: 1.US1B-E3/5AT.pdf 2.US1B-E3/5AT.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 99000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p> |
|  | |
| <p>Image may be representation. See specs for product details.</p> | |

Spezifikationen

| | |
|------------------------------------|---|
| Teilenummer | US1B-E3/5AT |
| Hersteller | Vishay / Semiconductor - Diodes Division |
| Beschreibung | DIODE GEN PURP 100V 1A DO214AC |
| Kategorie | Diskrete Halbleiterprodukte > Dioden-Gleichrichter- |
| Teilstatus | 99000 pcs Stock |
| Serie | - |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | DO-214AC, SMA |
| Supplier Device-Gehäuse | DO-214AC (SMA) |
| Diodentyp | Standard |
| Strom - Richt (Io) | 1A |
| Spannung - Forward (Vf) (Max) @ If | 1V @ 1A |
| Strom - Sperrleckstrom @ Vr | 10µA @ 100V |
| Spannung - Sperr (Vr) (max) | 100V |
| Geschwindigkeit | Fast Recovery = 200mA (Io) |
| Rückwärts-Erholzeit (Trr) | 50ns |
| Betriebstemperatur - Anschluss | -55°C ~ 150°C |
| Kapazität @ Vr, F | 15pF @ 4V, 1MHz |
| Verpackung | Tape & Reel (TR) |

US1B-E3/5AT ist neu im Original, Suche US1B-E3/5AT Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie US1B-E3/5AT Vishay / Semiconductor - Diodes Division mit Garantie und Vertrauen. Anfrage US1B-E3/5AT: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|---|--|---|
|  <p>US1B-13-F Diodes Incorporated DIODE GEN PURP 100V 1A SMA</p> |  <p>US1B-E3 VISHAYMAS US1B-E3 VISHAYMAS</p> |  <p>US1B-M3/5AT Vishay / Semiconductor - Diodes Division DIODE 1A 100V 50NS DO- 214AC</p> |  <p>US1B-E3/61T Vishay / Semiconductor - Diodes Division DIODE GEN PURP 100V 1A DO214AC</p> |
|  <p>US1B-13 Diodes Incorporated DIODE GEN PURP 100V 1A SMA</p> |  <p>US1B-M3/5AT Electro-Films (EFI) / Vishay DIODE GEN PURP 100V 1A DO214AC</p> |  <p>US1B T/R PANJIT US1B T/R PANJIT</p> |  <p>US1B-E3/61T Electro-Films (EFI) / Vishay DIODE GEN PURP 100V 1A DO214AC</p> |

heiße Teile

Mehr

- | | | | | |
|---------------|------------------------|---------------|---------------|---------------|
| ⊕ US168ELD | ↔ US168ESE | ⇒ US1881ESO | D US1881KSE | ↔ US1881KSO |
| ⊕ US1881KUA | ⊕ US1881KUA-AAA-000-BU | D US1881LSO | ⇒ US1A-13-F | ↔ US1A-E3/5AT |
| ⊕ US1A-E3/5AT | ⊕ US1A-E3/61T | ⊕ US1A-E3/61T | ↔ US1A-M3/61T | ↔ US1A-M3/61T |
| D US1AHE3/5AT | ⊕ US1AHE3/5AT | ⊕ US1AHE3/61T | ⊕ US1AHE3/61T | ↔ US1B-13-F |
| ⇒ US1B-E3/5AT | ↔ US1B-E3/61T | ⊕ US1B-E3/61T | ⊕ US1B-M3/61T | ↔ US1B-M3/61T |
| ↔ US1BHE3/5AT | ⇒ US1BHE3/5AT | D US1BHE3/61T | ⊕ US1BHE3/61T | ⊕ US1C-E3/61T |
| ⊕ US1D-13-F | D US1D-E3/61T | ⇒ US1D-E3/61T | ↔ US1D-M3/61T | ↔ US1D-M3/61T |
| ⊕ US1DWF-7 | ⊕ US1DWF-7 | ↔ US1G-13-F | ⇒ US1G-E3/61T | ↔ US1G-E3/61T |
| ⊕ US1G-M3/61T | ⊕ US1G-M3/61T | ⊕ US1G/11T | D US1GHE3/5AT | ↔ US1GHE3/5AT |
| ↔ US1GHE3/61 | ⊕ US1GHE3/61T | ⊕ US1GHE3/61T | ⊕ US1GHE3_A/H | ↔ US1GHE3_A/H |

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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